

P-Channel Power MOSFET

-30V, -5.3A, $60m\Omega$

FEATURES

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low Onresistance
- Compliant to RoHS Directive 2011/65/EU and WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

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- Load Switch
- PA Switch

KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
V _{DS}		-30	V	
5 / \	V _{GS} = -10V	60		
$R_{DS(on)}(max)$	V _{GS} = -4.5V	90	mΩ	
Q_g		9.52	nC	

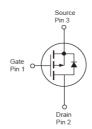












Notes: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V _{DS}	-30	V	
Gate-Source Voltage	V_{GS}	±20	V	
Out to Note 1)	T _C = 25°C		-5.3	
Continuous Drain Current, V _{GS} @4.5V ^(Note 1)	T _C = 100°C	I _D	-3.2	A
Pulsed Drain Current, V _{GS} @4.5V (Note 2)	I _{DM}	-20	А	
Total Power Dissipation @ T _C = 25°C	P _{DTOT}	2.5	W	
Operating Junction and Storage Temperature	T _J , T _{STG}	- 55 to +150	°C	

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction to Case Thermal Resistance	R _{eJC}	30	°C/W		
Junction to Ambient Thermal Resistance	R _{⊕JA}	50	°C/W		

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.

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ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 3)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250\mu A$	BV _{DSS}	-30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1.0	-1.5	-3.0	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -24V, V_{GS} = 0V$	I _{DSS}	-		-1	μA
Desir Course On Otata Basistanas	$V_{GS} = -10V, I_D = -5.3A$			50	60	mΩ
Drain-Source On-State Resistance	$V_{GS} = -4.5V, I_D = -4.2A$	$R_{DS(ON)}$		75	90	
Dynamic (Note 4)						
Total Gate Charge	15)/ 1 5 6 4	Q_g		9.52		
Gate-Source Charge	$V_{DS} = -15V, I_D = -5.3A,$ $V_{GS} = -10V$	Q_{gs}		3.43		nC
Gate-Drain Charge	V _{GS} 10 V	Q_{gd}		1.71		
Input Capacitance	45)(1)(C _{iss}		551.57		
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		90.96		pF
Reverse Transfer Capacitance	1 - 1.0IVITZ	C _{rss}		60.79		
Switching (Note 5)						
Turn-On Delay Time		t _{d(on)}		10.8		
Turn-On Rise Time	$V_{DD} = -15V$, $R_{GEN} = 6\Omega$,	t _r		2.33		
Turn-Off Delay Time	$I_D = -1A$, $V_{GS} = -10V$,	$t_{d(off)}$		22.53		ns
Turn-Off Fall Time		t _f		3.87		
Source-Drain Diode (Note 3)						
Forward On Voltage	I _S = -1.9A, V _{GS} = 0V	V_{SD}			-1.3	V

Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. Pulse test: PW ≤ 300µs, duty cycle ≤ 2%
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature.

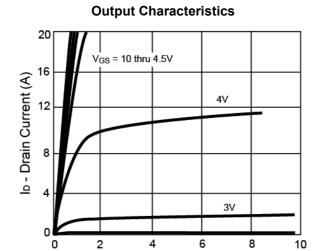
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING		
TSM9435CS RLG	SOP-8	2,500pcs / 13" Reel		



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$



V_{DS} - Drain-to-Source Voltage (V)

Transfer Characteristics

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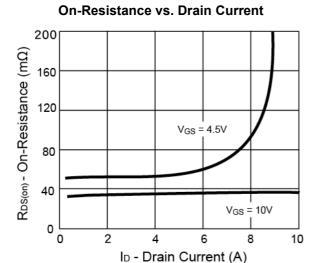
(Y) transfer Characteristics

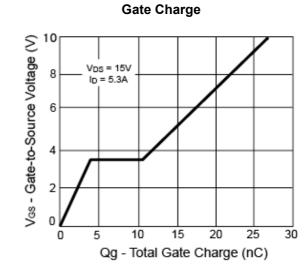
125°C

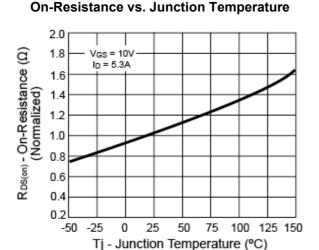
125°C

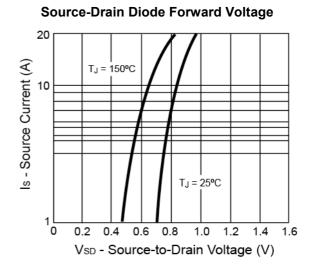
Tc = -55°C

Vos - Gate-to-Source Voltage (V)









Version: D1602

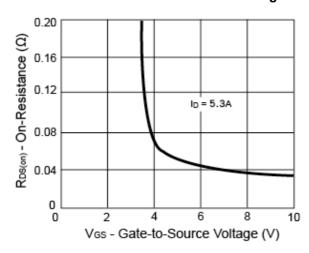
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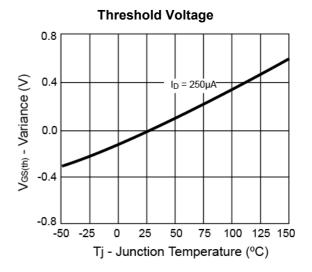


CHARACTERISTICS CURVES

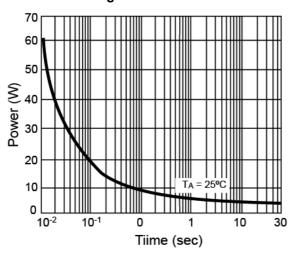
(T_A = 25°C unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

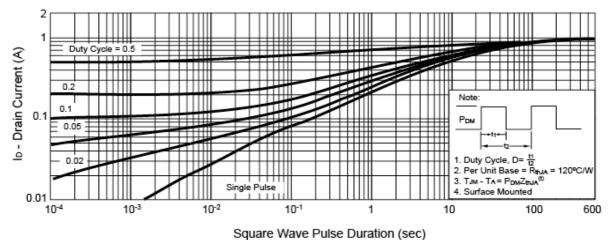




Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

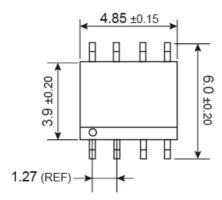


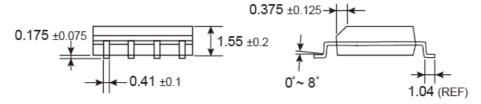
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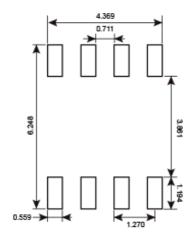
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

SOP-8

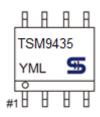




SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr S =May T =Jun U =Jul V =Aug

W = Sep X = Oct Y = Nov Z = Dec

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L = Lot Code (1~9, A~Z)



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